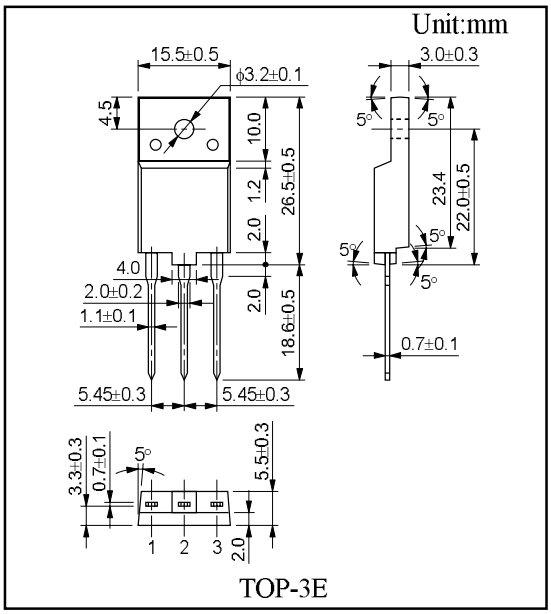
2SC5657

■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	1500	V
Collector to emitter voltage	V_{CES}	1500	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	8*3	A
Collector current	I_C	4	A
Base current	I_B	2	A
Collector power dissipation	P_C	40*1 / 3*2	W
Junction temperature	Tj	150	°C
Storage temperature		-55 to +150	°C



*1)TC=25°C ,*2)Ta=25°C(Without heat sink)
*3)Non-repetitive peak collector current.

■ Electrical Characteristics(Tc=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB}=1000V,I_E=0	-	-	50	μA
	I_{CBO}	V_{CB}=1500V,I_E=0	-	-	1	mA
Emitter to base voltage	V_{EBO}	I_E=500mA,I_C=0	7	-	-	V
Forward current transfer ratio	f_{FE}	V_{CE}=5V,I_C=2A	5	-	9	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C=2A,I_B=0.5A	-	-	5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	I_C=2A,I_B=0.5A	-	-	1.5	V
Transition frequency	f_T	V_{CE}=10V,I_C=0.1A,f=0.5MHz	-	3	-	MHz
Storage time	T_{stg}	I_C=2A,I_{B1}=0.4A,I_{B2}=-0.8A	-	-	5.0	μs
Fall time	T_f	I_C=2A,I_{B1}=0.4A,I_{B2}=-0.8A	-	-	0.5	μs
Diode characteristics	V_F		-	-	-2	V